

# IRLI2203NPbF

HEXFET® Power MOSFET

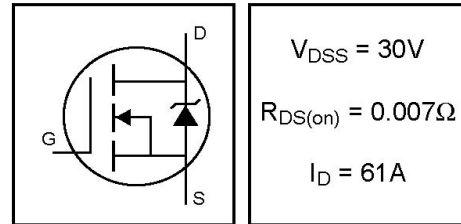
- Logic-Level Gate Drive
- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ③
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated

• Lead-Free

### Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

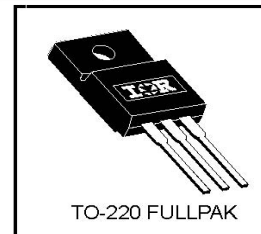
The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.



$$V_{DSS} = 30V$$

$$R_{DS(on)} = 0.007\Omega$$

$$I_D = 61A$$



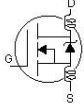
### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	61	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	43	
$I_{DM}$	Pulsed Drain Current ①⑥	400	
$P_D @ T_C = 25^\circ C$	Power Dissipation	47	W
	Linear Derating Factor	0.31	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 16$	V
$E_{AS}$	Single Pulse Avalanche Energy ②⑥	390	mJ
$I_{AR}$	Avalanche Current ①⑥	60	A
$E_{AR}$	Repetitive Avalanche Energy ①	4.7	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑥	1.2	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Mounting torque, 6-32 or M3 screw	10 lbf·in (1.1N·m)	

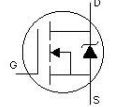
### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	3.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient	---	65	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	---	---	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	---	0.035	---	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⓐ
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	---	---	0.007	$\Omega$	$V_{GS} = 10V, I_D = 37A$ ④
		---	---	0.01		$V_{GS} = 4.5V, I_D = 31A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	---	---	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	47	---	---	S	$V_{DS} = 25V, I_D = 60A$ ⓐ
$I_{DSS}$	Drain-to-Source Leakage Current	---	---	25	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
		---	---	250		$V_{DS} = 24V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	---	---	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	---	---	-100		$V_{GS} = -16V$
$Q_g$	Total Gate Charge	---	---	110	nC	$I_D = 60A$
$Q_{gs}$	Gate-to-Source Charge	---	---	31		$V_{DS} = 24V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	---	---	57		$V_{GS} = 4.5V$ , See Fig. 6 and 13 ④ⓐ
$t_{d(on)}$	Turn-On Delay Time	---	15	---	ns	$V_{DD} = 15V$
$t_r$	Rise Time	---	210	---		$I_D = 60A$
$t_{d(off)}$	Turn-Off Delay Time	---	29	---		$R_G = 1.8\Omega, V_{GS} = 4.5V$
$t_f$	Fall Time	---	54	---		$R_D = 0.25\Omega$ , See Fig. 10 ④ⓐ
$L_D$	Internal Drain Inductance	---	4.5	---	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	---	7.5	---		
$C_{iss}$	Input Capacitance	---	3500	---	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	---	1400	---		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	---	690	---		$f = 1.0\text{MHz}$ , See Fig. 5ⓐ
C	Drain to Sink Capacitance	---	12	---		$f = 1.0\text{MHz}$

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	---	---	61	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①ⓐ	---	---	400		
$V_{SD}$	Diode Forward Voltage	---	---	1.3	V	$T_J = 25^\circ\text{C}, I_S = 37A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	---	94	140	ns	$T_J = 25^\circ\text{C}, I_F = 60A$
$Q_{rr}$	Reverse Recovery Charge	---	280	410	$\mu C$	$di/dt = 100A/\mu s$ ④ⓐ
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

## Specification changes

Rev. #	Parameters	Old spec.	New spec.	Comments	Revision Date
1	$V_{GS(th)}$ (Max.)	2.5V	No spec.	Removed $V_{GS(th)}$ Max. Specification	11/1/96
1	$V_{GS}$ (Max.)	$\pm 20$	$\pm 16$	Decrease $V_{GS}$ Max. Specification	11/1/96

### Notes:

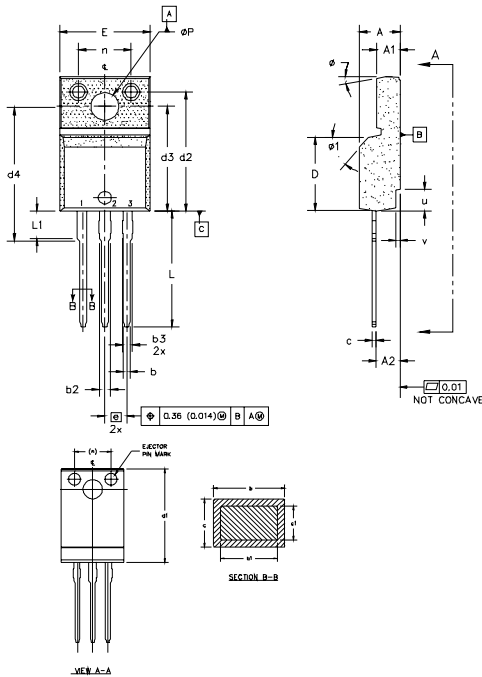
- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ②  $V_{DD} = 15V$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 220\mu H$   
 $R_G = 25\Omega, I_{AS} = 60A$ . (See Figure 12)
- ③  $I_{SD} \leq 60A, di/dt \leq 140A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤  $t = 60s, f = 60\text{Hz}$       ⑥ Uses IRL2203N data and test conditions

# IRLI2203NPbF



## TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



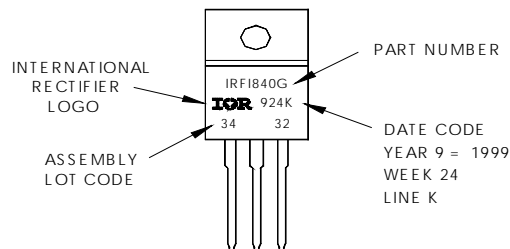
- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  - 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5.0 DIMENSION b1 APPLY TO BASE METAL ONLY.
  - 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
  - 7.0 CONTROLLING DIMENSION - INCHES.

SYMBOL	DIMENSIONS				NOTES	LEAD ASSIGNMENTS
	MILLIMETERS		INCHES			
A	4.57	4.83	0.180	0.190		
A1	2.57	2.83	0.101	0.114		
A2	2.51	2.85	0.099	0.112		
d	0.622	0.89	0.024	0.035		
b1	0.622	0.838	0.024	0.033	5	
b2	1.229	1.400	0.048	0.055		
b3	1.229	1.400	0.048	0.055		
c	0.440	0.629	0.017	0.025		
c1	0.440	0.584	0.017	0.023		
D	8.65	9.80	0.341	0.386	4	
d1	15.80	16.12	0.622	0.635		
d2	13.97	14.22	0.550	0.560		
d3	12.30	12.92	0.484	0.509		
d4	8.64	9.91	0.340	0.390		
E	10.36	10.63	0.408	0.419	4	
e	2.54 BSC		0.100 BSC			
L	13.20	13.73	0.520	0.541		
L1	3.10	3.50	0.122	0.138	3	
n	6.09	6.19	0.238	0.242		
phi P	3.05	3.45	0.120	0.136		
u	2.40	2.50	0.094	0.098	6	
v	0.40	0.50	0.016	0.020	6	
w	3"	7"	3"	7"		
phi 1	45°	45°	45°	45°		

## TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW 24 1999  
IN THE ASSEMBLY LINE "K"

**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

